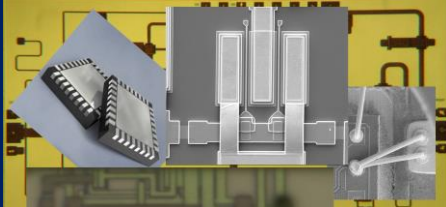


TMC213

43-46 GHz

Power Amplifier



Product Features

- RF frequency: 43 to 46 GHz
- Linear Gain: 21 dB
- Psat: 20 W
- Die Size: X=3 mm, Y=2 mm
- 0.15um GaN HEMT Process
- 4 mil SiC substrate
- DC Power: 24 VDC, 3.1 A

Application

- 5G Wireless
- SATCOM
- Military Radar, EW

Product Description

The TMC213 GaN HEMT Power amplifier is a three-stage Single-ended power MMIC, designed for use in 5G wireless, SATCOM and Military Radar and EW applications. The TMC213 is a 50 Ω matched design which eliminates the need for RF port matching. To ensure rugged and reliable operation and moisture protection, the TMC213 is fully passivated. Both bond pad and backside metallization are Au-based that is compatible with ribbon and wedge bonding and high conductivity epoxy and eutectic die attach methods.

Electrical Performance : Vdd = 24 V, Vgg = -4.0 V, TA = 25 °C, F = 44.5 GHz

	min	Typ	Max	Units
Frequency	43		46	GHz
Gain		21		dB
P1dB		41		dBm
Psat		43		dBm
PAE		27		%
OIP3		48		dBm
Bias Voltage		24		V
Bias Current		3100		mA

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